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Correction: High throughput first-principles calculations of bixbyite oxides for TCO applications

Nasrin Sarmadian,^{*a} Rolando Saniz,^a Bart Partoens,^a Dirk Lamoen,^b Kalpana Voley,^c Guido Huyberegts^c and Johan Paul^c

Correction for 'High throughput first-principles calculations of bixbyite oxides for TCO applications' by Nasrin Sarmadian *et al.*, *Phys. Chem. Chem. Phys.*, 2014, **16**, 17724–17733.

In all our calculations with the hybrid functional HSE06 the default value of 0.25 for the amount of exact exchange was adjusted to 0.325 in order to reproduce the experimentally available fundamental band gap of In_2O_3 .

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^a CMT, Departement Fysica, Universiteit Antwerpen, Groenenborgerlaan 171, B-2020 Antwerpen, Belgium. E-mail: nasrin.sarmadian@uantwerpen.be; Fax: +32-3-2653542; Tel: +32-3-2653439

^b EMAT, Departement Fysica, Universiteit Antwerpen, Groenenborgerlaan 171, B-2020 Antwerpen, Belgium. Fax: +32-3-2653542; Tel: +32-3-2653439

^c Flamac, a division of SIM, Technologiepark 903, 9052 Zwijnaarde, Belgium

